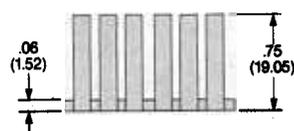
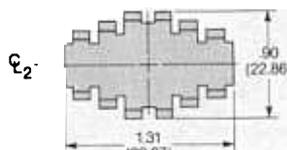


# SECTION 2

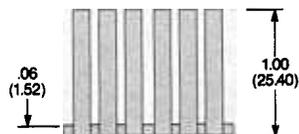
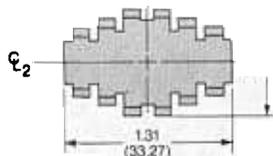
## HEAT DISSIPATORS FOR PLASTIC CASE, CASE-MOUNTED SEMICONDUCTORS

### LA-A3 Series

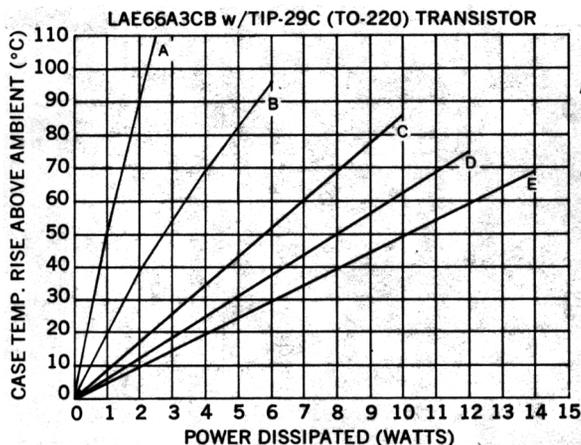


Dimensions are for reference use only. Contact IERC for dimensions with tolerances or standard part drawings.

### LA-A4 Series



Dimensions are for reference use only. Contact IERC for dimensions with tolerances or standard part drawings.



#### DESCRIPTION OF CURVES

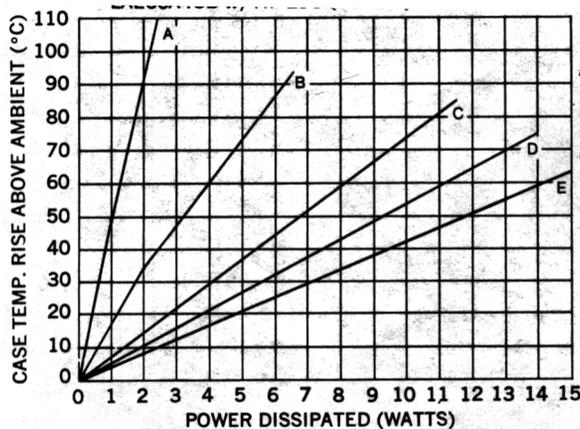
- A. N.C. Horiz. Device Only Mounted to G-10.
- B. N.C. Horiz. & Vert. With Dissipator.
- C. 200 FPM w/Diss.
- D. 500 FPM w/Diss.
- E. 1000 FPM w/Diss.

- Thermal Resistance Case to Sink is 0.9-1.1 °C/W w/Joint Compound.
- Derate 0.5 °C/watt for unplated part in natural convection only.
- Derate 3.0 °C/watt for Insulube® part in natural convection only.

#### Ordering Information

IERC PART NO.				Semiconductor Accommodated	Hole patt. ref. no. (see pg. 2-27)	Max. Weight (Grams)
Unplated	Comm'l. Black Anodize	Mil. Black Anodize	Insulube® 448			
LA000A3U LAE66A3U	LA000A3CB LAE66A3CB	LA000A3B LAE66A3B	LA000A3 LAE66A3	Undrilled TO-126, TO-220	— 1	6.1 6.1

Note: See page iv for other finishes.



#### DESCRIPTION OF CURVES

- A. N.C. Horiz. Device Only Mounted to G-10.
- B. N.C. Horiz. & Vert. With Dissipator.
- C. 200 FPM w/Diss.
- D. 500 FPM w/Diss.
- E. 1000 FPM w/Diss.

- Thermal Resistance Case to Sink is 0.9-1.1 °C/W w/Joint Compound.
- Derate 0.6 °C/watt for unplated part in natural convection only.
- Derate 3.0 °C/watt for Insulube® part in natural convection only.

IERC PART NO.				Semiconductor Accommodated	Hole patt. ref. no. (see pg. 2-27)	Max. Weight (Grams)
Unplated	Comm'l. Black Anodize	Mil. Black Anodize	Insulube® 448			
LA000A4U LAE66A4U	LA000A4CB LAE66A4CB	LA000A4B LAE66A4B	LA000A4 LAE66A4	Undrilled TO-126, TO-220	— 1	7.6 7.6

Note: See page iv for other finishes